

SIPMOS® Small-Signal-Transistor

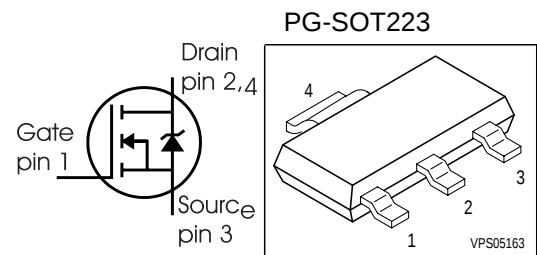
Feature

- N-Channel
- Enhancement mode
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101



Product Summary

V_{DS}	60	V
$R_{DS(on)}$	0.3	Ω
I_D	1.8	A



Type	Package	Tape and Reel Information	Marking	Packaging
BSP295	PG-SOT223	L6327: 1000 pcs/reel	BSP295	Non dry

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A=25\text{ °C}$ $T_A=70\text{ °C}$	I_D	1.8 1.44	A
Pulsed drain current $T_A=25\text{ °C}$	$I_{D\text{ puls}}$	7.2	
Reverse diode dv/dt $I_S=1.8\text{ A}$, $V_{DS}=40\text{ V}$, $di/dt=200\text{ A}/\mu\text{s}$, $T_{jmax}=150\text{ °C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
ESD class (JESD22-A114-HBM)		1B (>500V, <1000V)	
Power dissipation $T_A=25\text{ °C}$	P_{tot}	1.8	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C
IEC climatic category; DIN IEC 68-1		55/150/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	15	25	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	80	115	
@ 6 cm ² cooling area 1)		-	48	70	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0, I_D=250\mu A$	$V_{(BR)DSS}$	60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=400\mu A$	$V_{GS(th)}$	0.8	1.1	1.8	
Zero gate voltage drain current $V_{DS}=60V, V_{GS}=0, T_j=25^{\circ}C$ $V_{DS}=60V, V_{GS}=0, T_j=150^{\circ}C$	I_{DSS}	- -	- 8	0.1 50	μA
Gate-source leakage current $V_{GS}=20V, V_{DS}=0$	I_{GSS}	-	1	10	
Drain-source on-state resistance $V_{GS}=10V, I_D=1.8A$ $V_{GS}=4.5V, I_D=1.8A$	$R_{DS(on)}$	- -	0.22 0.39	0.3 0.5	Ω

¹⁾Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 1.44\text{A}$	0.8	1.7	-	S
Input capacitance	C_{iss}	$V_{GS} = 0$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	295	368	pF
Output capacitance	C_{oss}		-	95	118	
Reverse transfer capacitance	C_{rss}		-	45	67	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15\text{V}$, $V_{GS} = 4.5\text{V}$, $I_D = 1.44\text{A}$, $R_G = 15\Omega$	-	5.4	8.1	ns
Rise time	t_r		-	9.9	15	
Turn-off delay time	$t_{d(off)}$		-	27	41	
Fall time	t_f		-	19	28	

Gate Charge Characteristics

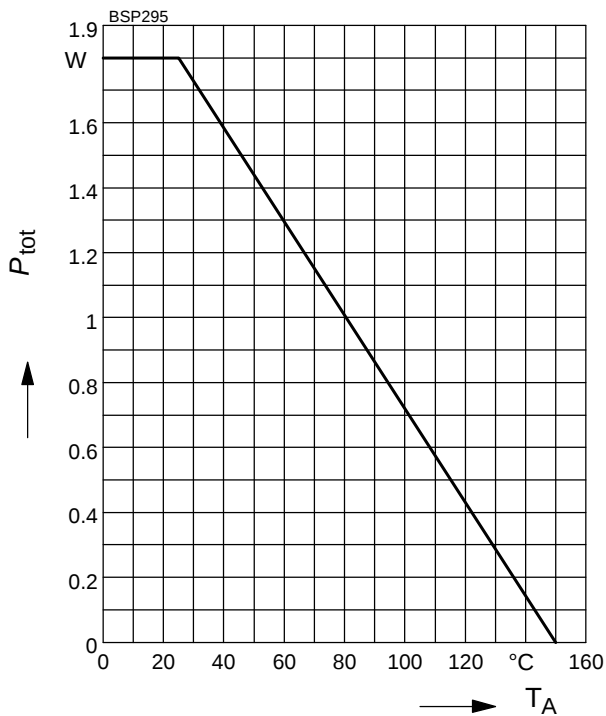
Gate to source charge	Q_{gs}	$V_{DD} = 24\text{V}$, $I_D = 1.8\text{A}$	-	0.9	1.1	nC
Gate to drain charge	Q_{gd}		-	5.6	8.4	
Gate charge total	Q_g	$V_{DD} = 24\text{V}$, $I_D = 1.8\text{A}$, $V_{GS} = 0$ to 10V	-	14	17	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 24\text{V}$, $I_D = 1.8\text{A}$	-	3.1	3.8	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_A = 25^{\circ}\text{C}$	-	-	1.8	A
Inv. diode direct current, pulsed	I_{SM}		-	-	7.2	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0$, $I_F = I_S$	-	0.84	1.3	V
Reverse recovery time	t_{rr}	$V_R = 25\text{V}$, $I_F = I_S$, $di_F/dt = 100\text{A}/\mu\text{s}$	-	36	45	ns
Reverse recovery charge	Q_{rr}		-	38	48	nC

1 Power dissipation

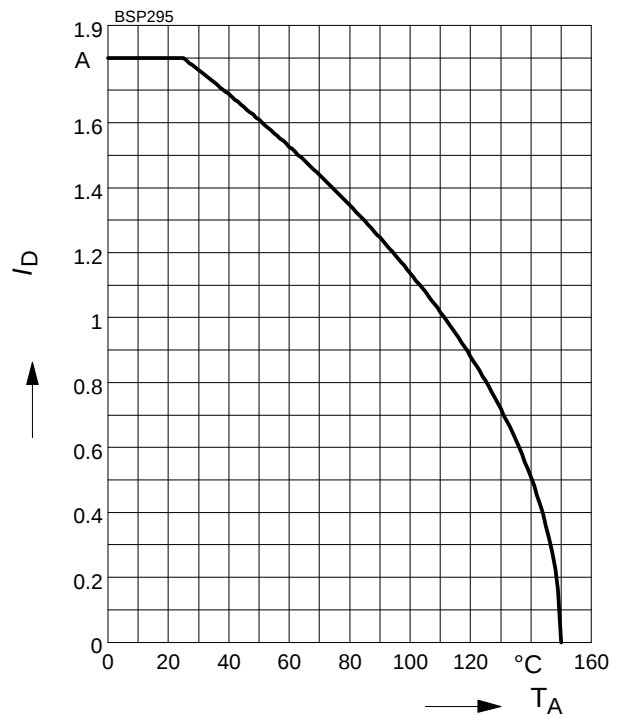
$$P_{\text{tot}} = f(T_A)$$



2 Drain current

$$I_D = f(T_A)$$

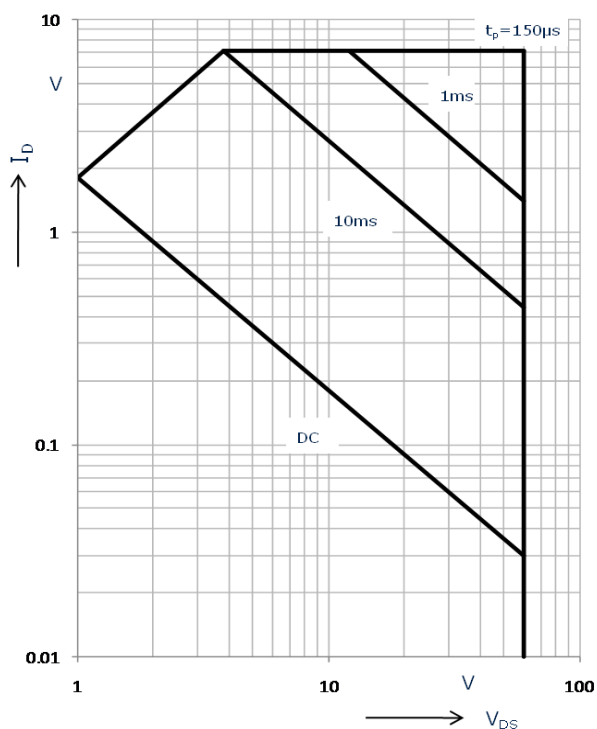
parameter: $V_{GS} \geq 10$ V



3 Safe operating area

$$I_D = f(V_{DS})$$

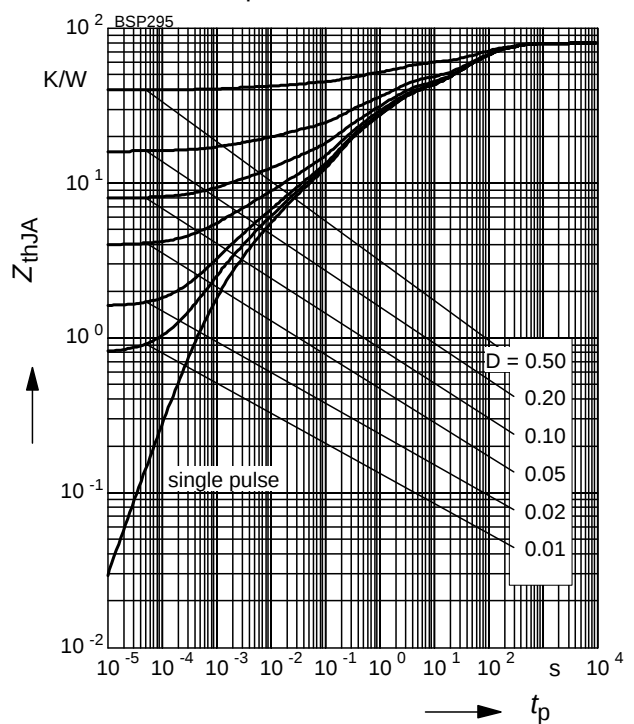
parameter: $D = 0$, $T_A = 25$ °C



4 Transient thermal impedance

$$Z_{\text{thJA}} = f(t_p)$$

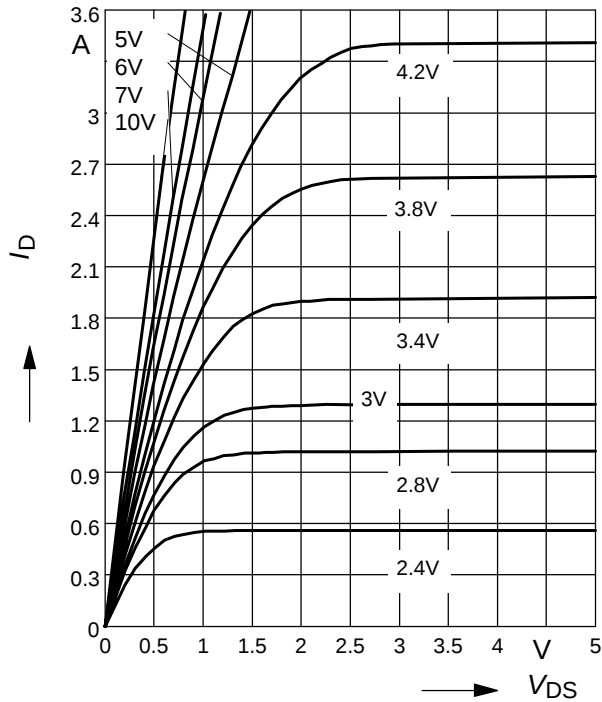
parameter: $D = t_p/T$



5 Typ. output characteristic

$$I_D = f(V_{DS})$$

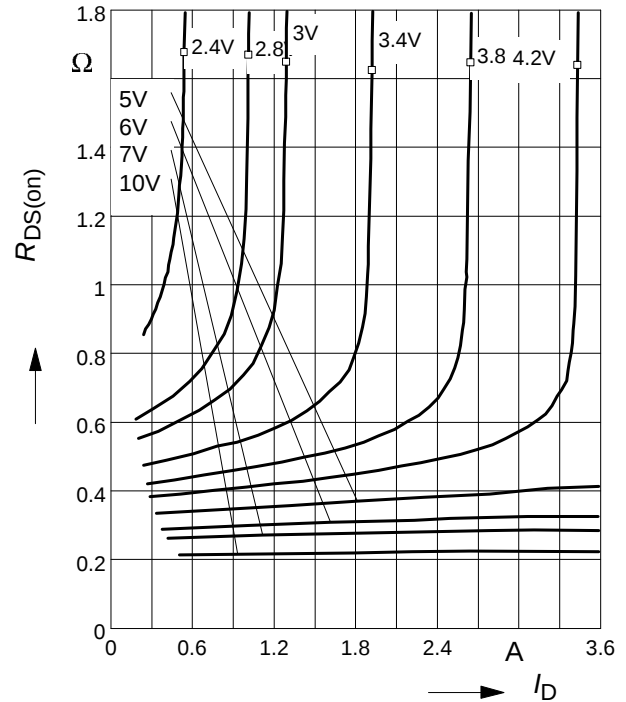
parameter: $T_j = 25\text{ }^{\circ}\text{C}$, V_{GS}



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

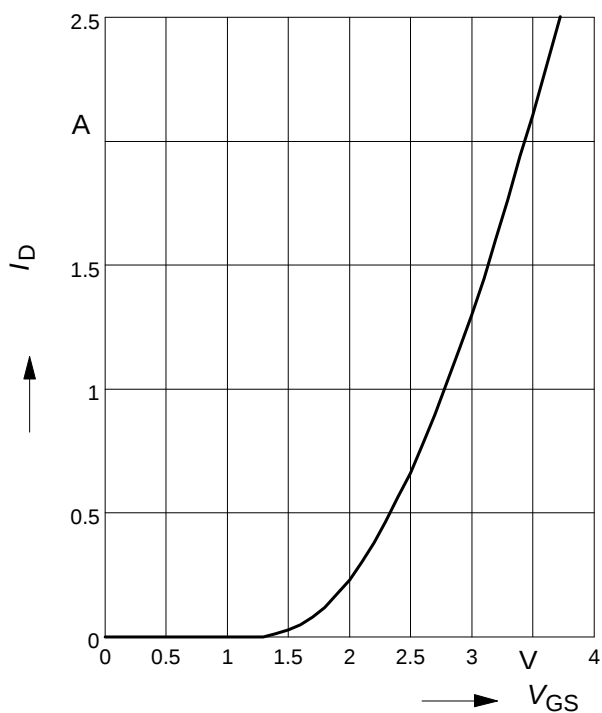
parameter: $T_j = 25\text{ }^{\circ}\text{C}$, V_{GS}



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

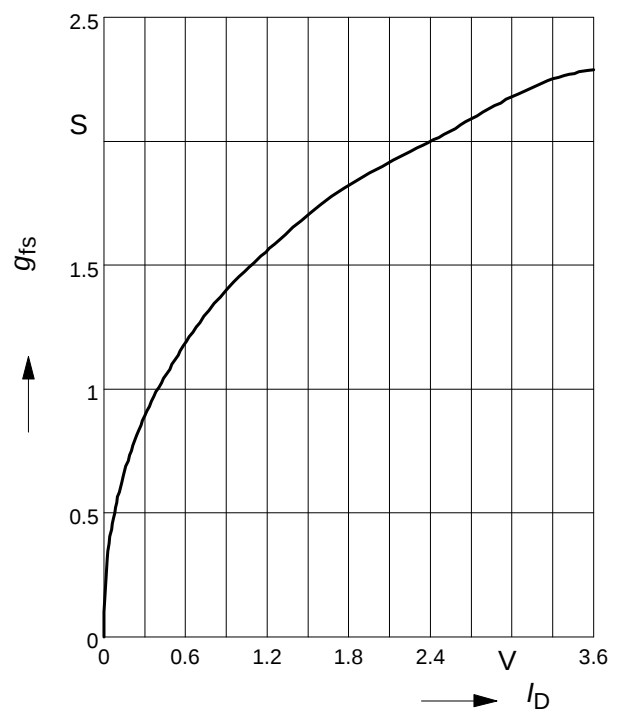
parameter: $T_j = 25\text{ }^{\circ}\text{C}$



8 Typ. forward transconductance

$$g_{fs} = f(I_D)$$

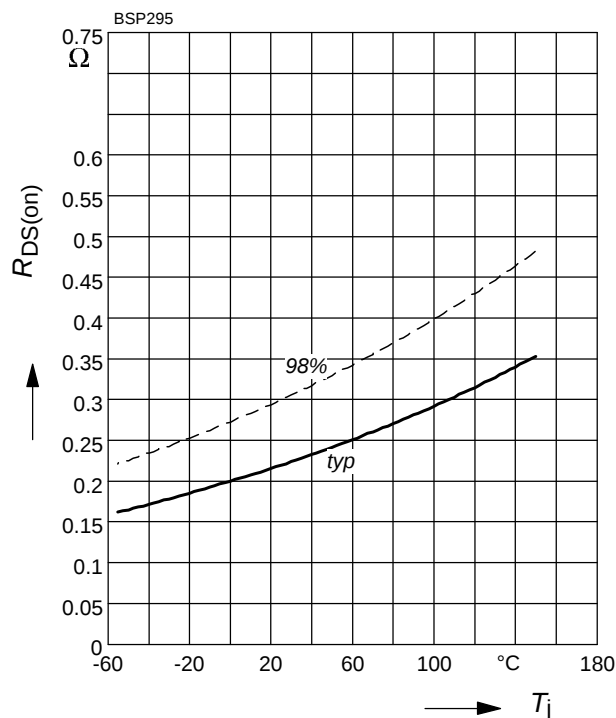
parameter: $T_j = 25\text{ }^{\circ}\text{C}$



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

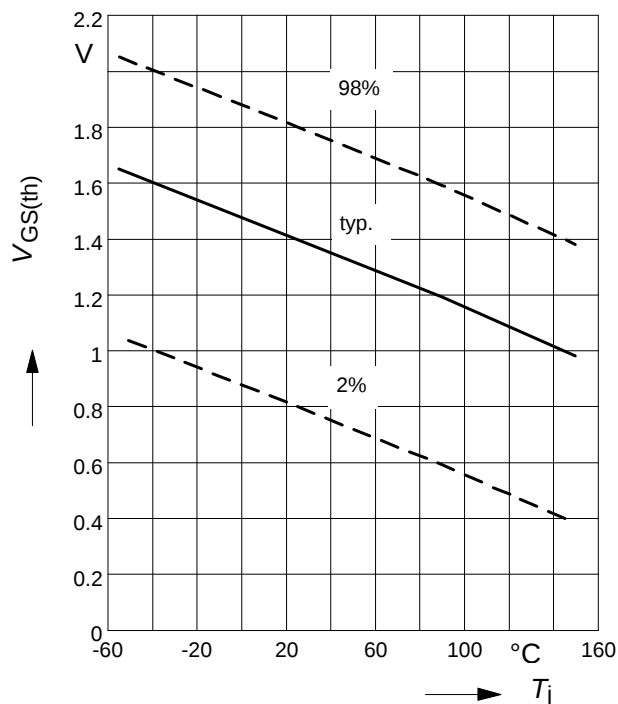
parameter: $I_D = 1.8 \text{ A}$, $V_{GS} = 10 \text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

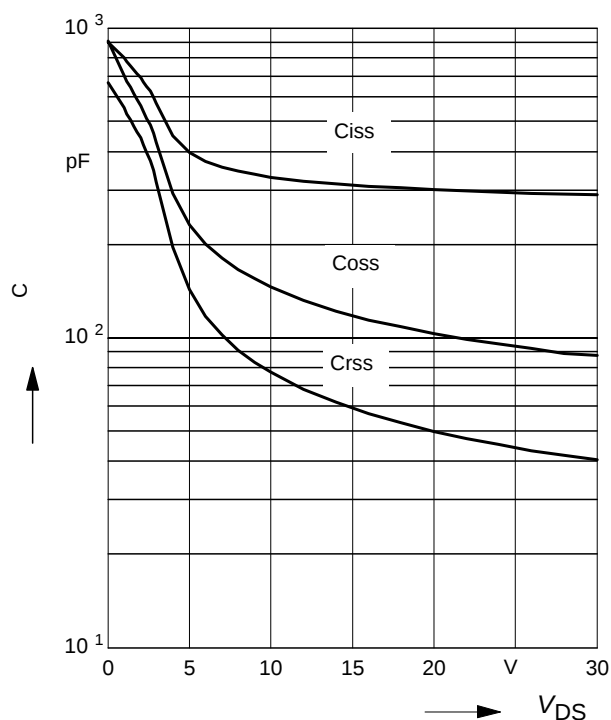
parameter: $V_{GS} = V_{DS}$; $I_D = 1 \text{ mA}$



11 Typ. capacitances

$$C = f(V_{DS})$$

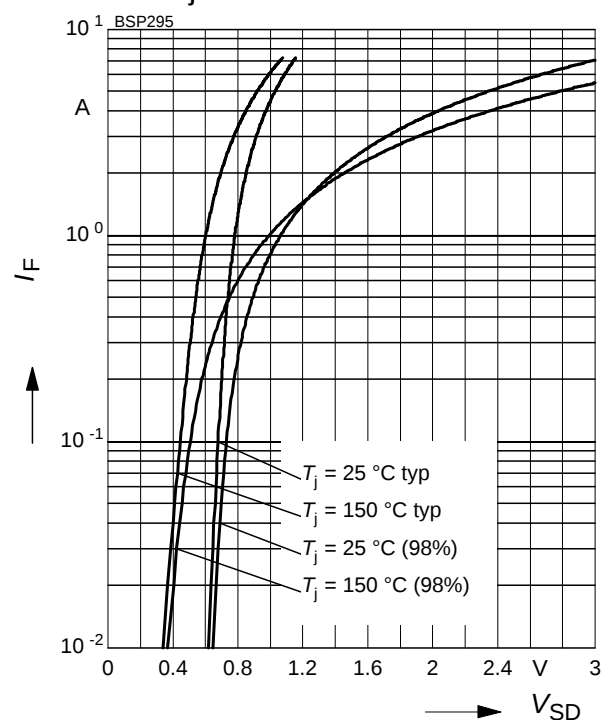
parameter: $V_{GS}=0$, $f=1 \text{ MHz}$, $T_j = 25^{\circ}\text{C}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

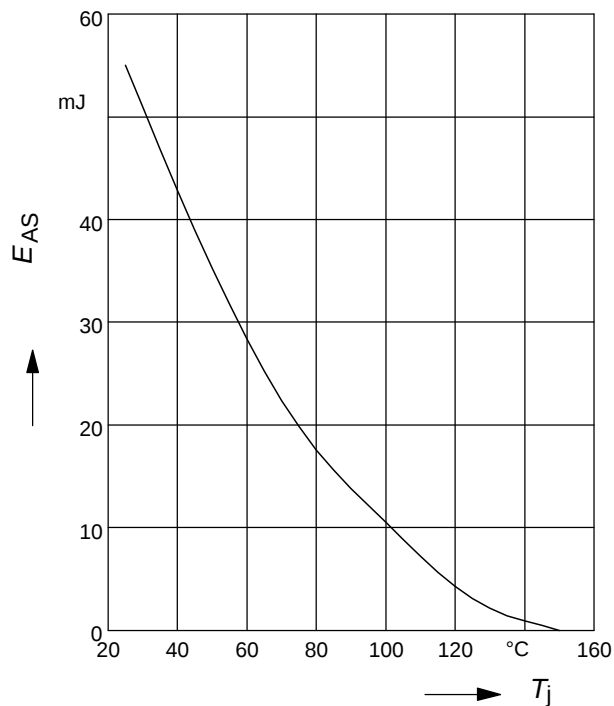
parameter: T_j



13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

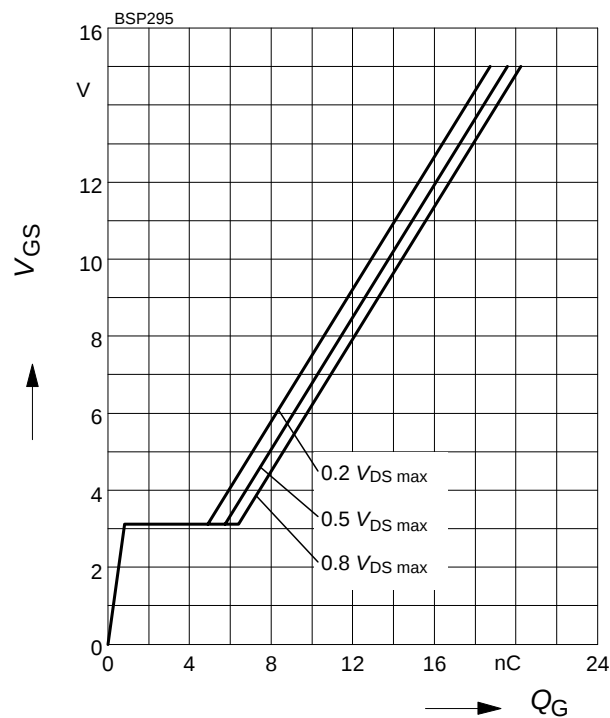
par.: $I_D = 3.9 \text{ A}$, $V_{DD} = 25 \text{ V}$, $R_{GS} = 25 \Omega$



14 Typ. gate charge

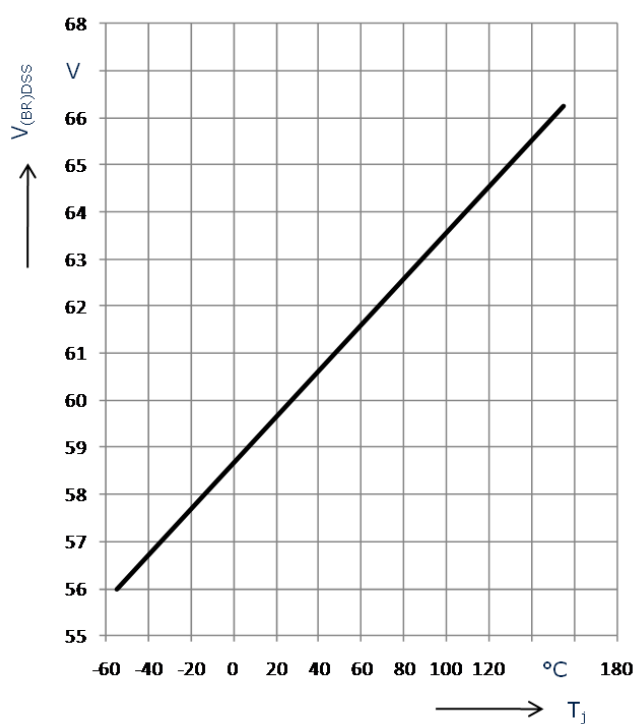
$$V_{GS} = f(Q_G); \text{ parameter: } V_{DS},$$

$I_D = 1.8 \text{ A pulsed}$, $T_j = 25 \text{ °C}$



15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



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